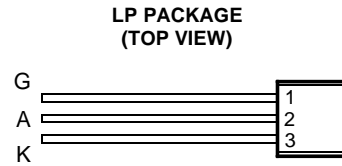
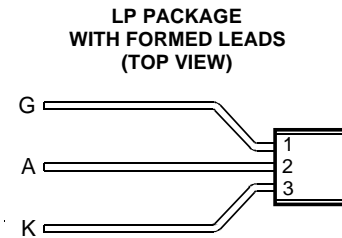


- 2 A Continuous On-State Current
- 15 A Surge-Current
- Glass Passivated Wafer
- 400 V to 600 V Off-State Voltage
- Max I_{GT} of 200 μ A
- Package Options

PACKAGE	PACKING	PART # SUFFIX
LP	Bulk	(None)
LP with fomed leads	Tape and Reel	R



MDC1AA



MDC1AB

absolute maximum ratings over operating case temperature (unless otherwise noted)

RATING		SYMBOL	VALUE	UNIT
Repetitive peak off-state voltage (see Note 1)	TICP106D	V_{DRM}	400	V
	TICP106M		600	
Repetitive peak reverse voltage	TICP106D	V_{RRM}	400	V
	TICP106M		600	
Continuous on-state current at (or below) 85°C case temperature (see Note 2)		$I_{T(RMS)}$	2	A
Surge on-state current (see Note 3)		I_{TSM}	15	A
Peak positive gate current (pulse width \leq 300 μ s)		I_{GM}	0.2	A
Average gate power dissipation (see Note 4)		$P_{G(AV)}$	0.3	W
Operating case temperature range		T_C	-40 to +110	°C
Storage temperature range		T_{stg}	-40 to +125	°C
Lead temperature 3.2 mm from case for 10 seconds		T_L	230	°C

- NOTES: 1. These values apply when the gate-cathode resistance $R_{GK} = 1 \text{ k}\Omega$.
2. These values apply for continuous dc operation with resistive load. Above 85°C derate linearly to zero at 110°C .
3. This value applies for one 50 Hz half-sine-wave when the device is operating at (or below) the rated value of peak reverse voltage and on-state current. Surge may be repeated after the device has returned to original thermal equilibrium.
4. This value applies for a maximum averaging time of 20 ms.

PRODUCT INFORMATION

Information is current as of publication date. Products conform to specifications in accordance with the terms of Power Innovations standard warranty. Production processing does not necessarily include testing of all parameters.



TICP106 SERIES SILICON CONTROLLED RECTIFIERS

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electrical characteristics at 25°C case temperature (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
I_{DRM}	Repetitive peak off-state current	$V_D = \text{rated } V_{DRM}$	$R_{GK} = 1 \text{ k}\Omega$			20	μA
I_{RRM}	Repetitive peak reverse current	$V_R = \text{rated } V_{RRM}$	$I_G = 0$			200	μA
I_{GT}	Gate trigger current	$V_{AA} = 6 \text{ V}$	$R_L = 100 \Omega$ $R_{GK} = 1 \text{ k}\Omega$			60	μA
V_{GT}	Gate trigger voltage	$V_{AA} = 6 \text{ V}$	$R_L = 100 \Omega$ $R_{GK} = 1 \text{ k}\Omega$	0.4		1	V
I_H	Holding current	$V_{AA} = 6 \text{ V}$	$R_{GK} = 1 \text{ k}\Omega$			5	mA
V_{TM}	Peak on-state voltage	$I_{TM} = 1 \text{ A}$	(see Note 5)			1.5	V

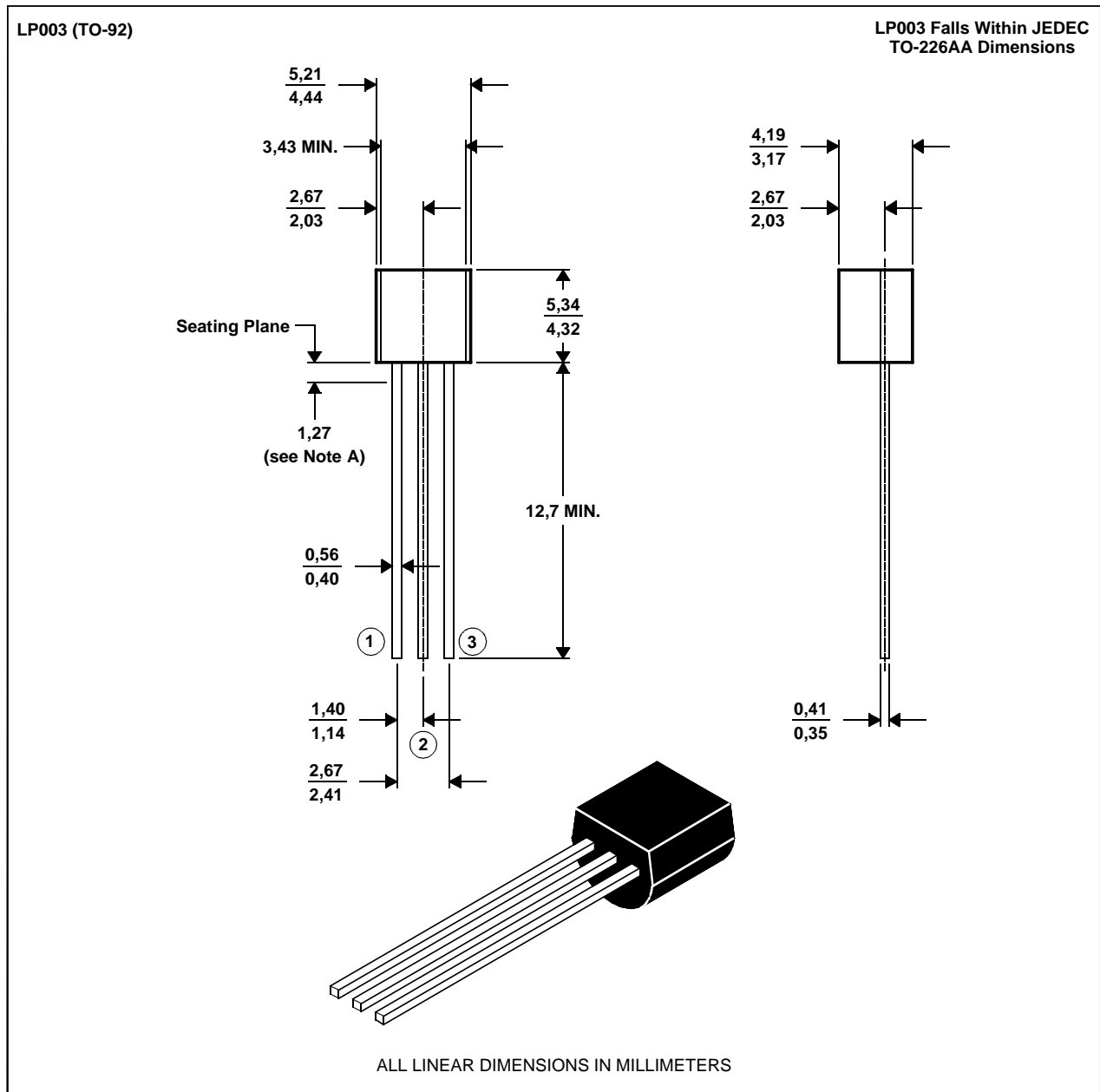
NOTE 5: This parameter must be measured using pulse techniques, $t_p = 1 \text{ ms}$, duty cycle $\leq 2 \%$. Voltage sensing-contacts, separate from the current carrying contacts, are located within 3.2 mm from the device body.

MECHANICAL DATA

LP003 (TO-92)

3-pin cylindrical plastic package

This single-in-line package consists of a circuit mounted on a lead frame and encapsulated within a plastic compound. The compound will withstand soldering temperature with no deformation, and circuit performance characteristics will remain stable when operated in high humidity conditions. Leads require no additional cleaning or processing when used in soldered assembly.



NOTE A: Lead dimensions are not controlled in this area.

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TICP106 SERIES SILICON CONTROLLED RECTIFIERS

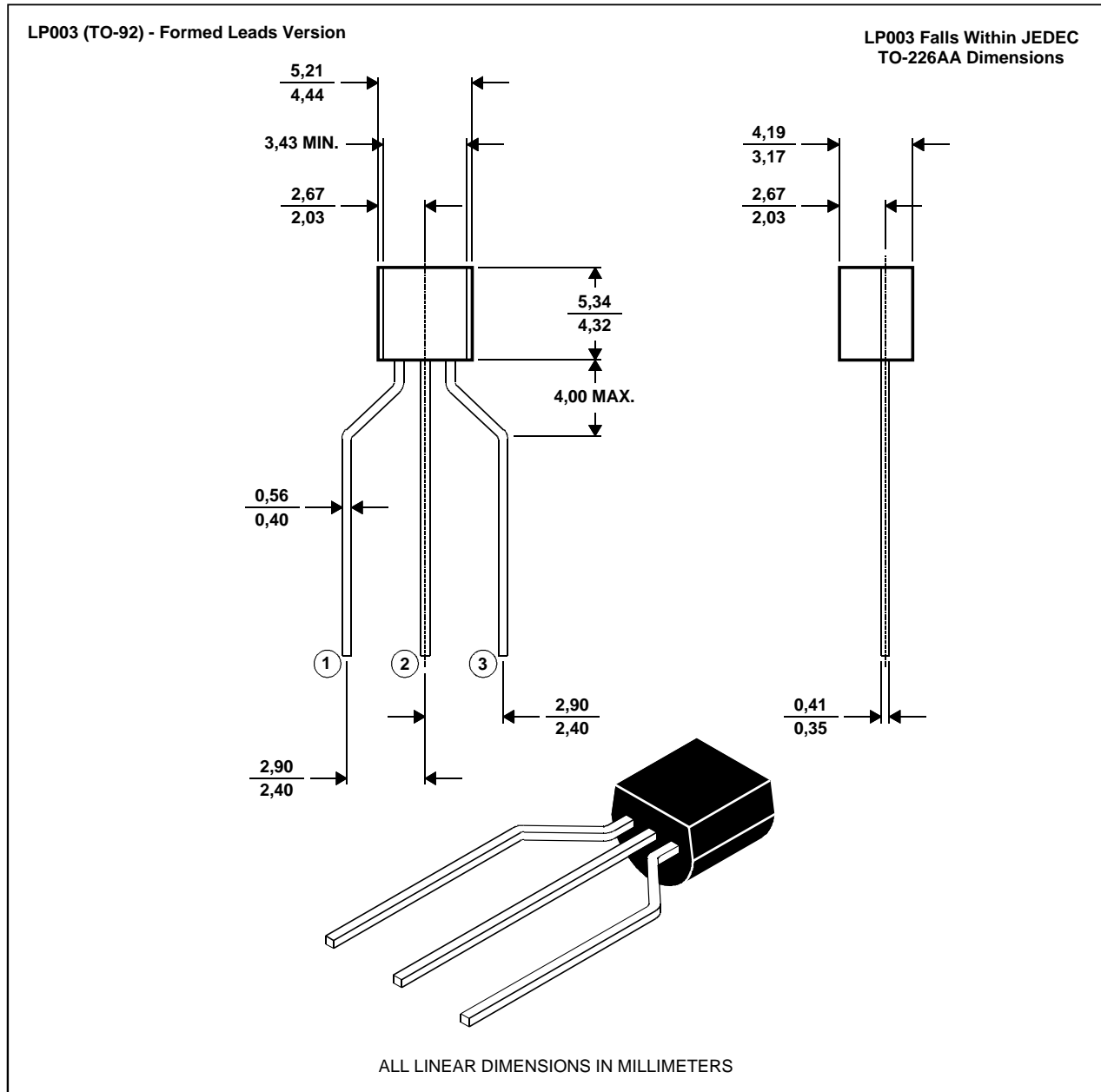
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MECHANICAL DATA

LP003 (TO-92)

3-pin cylindrical plastic package

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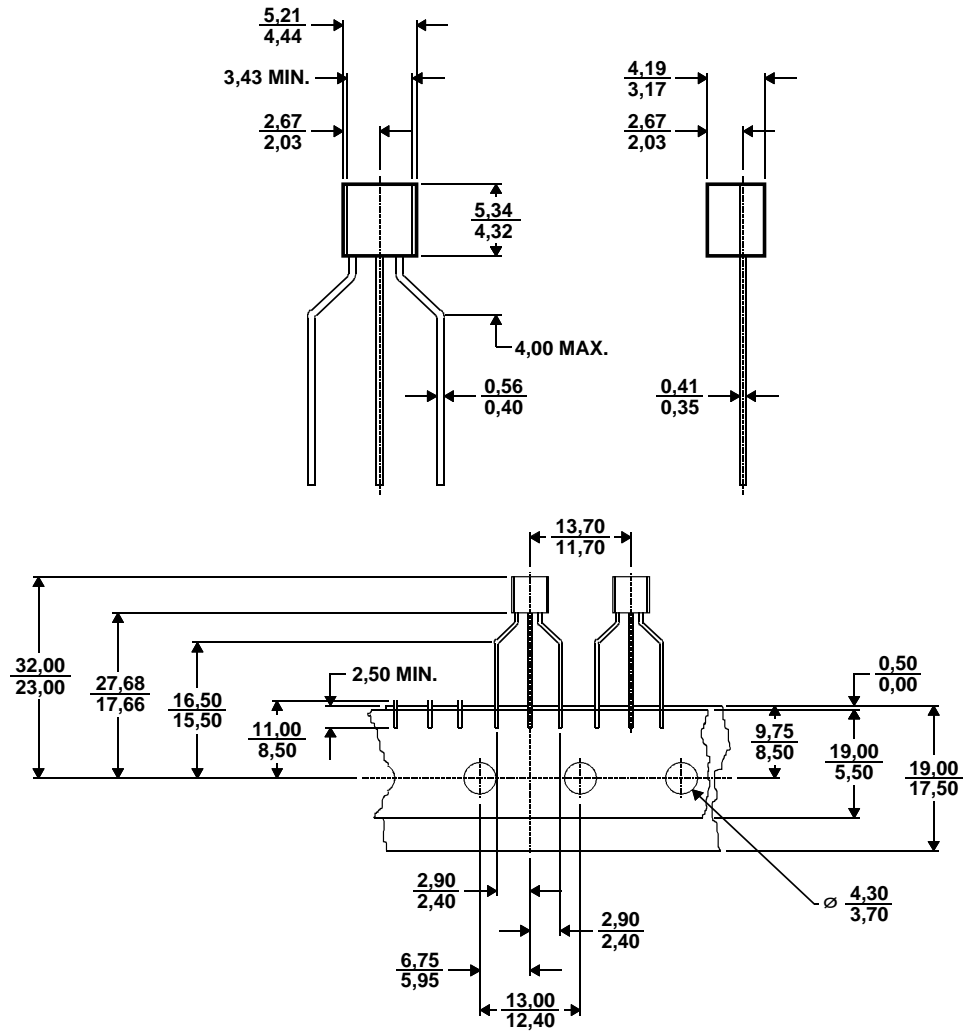
MDXXAR

PRODUCT INFORMATION

MECHANICAL DATA

LPR
tape dimensions

LP Package (TO-92) Tape (Formed Lead Version)



ALL LINEAR DIMENSIONS IN MILLIMETERS

MDXXAS

TICP106 SERIES SILICON CONTROLLED RECTIFIERS

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